

## Product Overview

### NGTB40N65IHL2: IGBT, 650V 40A FS2 Induction Heating

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for half bridge resonant applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

### Features

- Extremely Efficient Trench with Fieldstop Technology
- Low Switching Loss Reduces System Power Dissipation
- Optimized for Low Losses in IH Cooker Application
- $T_{Jmax} = 175^{\circ}C$
- Soft, Fast Free Wheeling Diode

### Applications

- Inductive Heating
- Soft Switching

### Part Electrical Specifications

Product	Compliance	Status	$V_{ES}$ Typ (V)	$I_C$ Max (A)	$V_{CE(sat)}$ Typ (V)	$V_F$ Typ (V)	$E_{off}$ Typ (mJ)	$E_{on}$ Typ (mJ)	$T_{rr}$ Typ (ns)	$I_{rr}$ Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand ( $\mu$ s)	$E_{AS}$ Typ (mJ)	$P_D$ Max (W)	Co- Pack aged Diode	Pack age Type
NGTB40N65IHL2WG	Pb-free	Active	650	45	1.8	1.2	0.36	-	465	36	135	-	-	300	Yes	TO-247-3
	Halide free															

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

Created on: 9/17/2019